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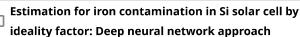
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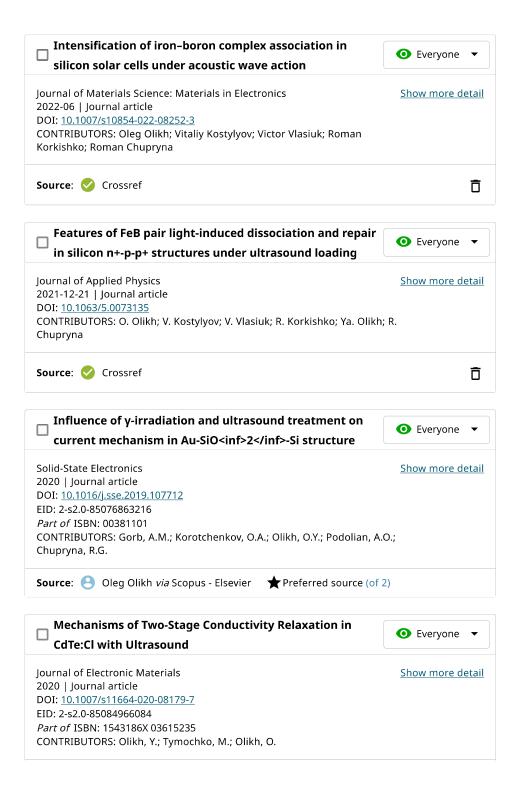
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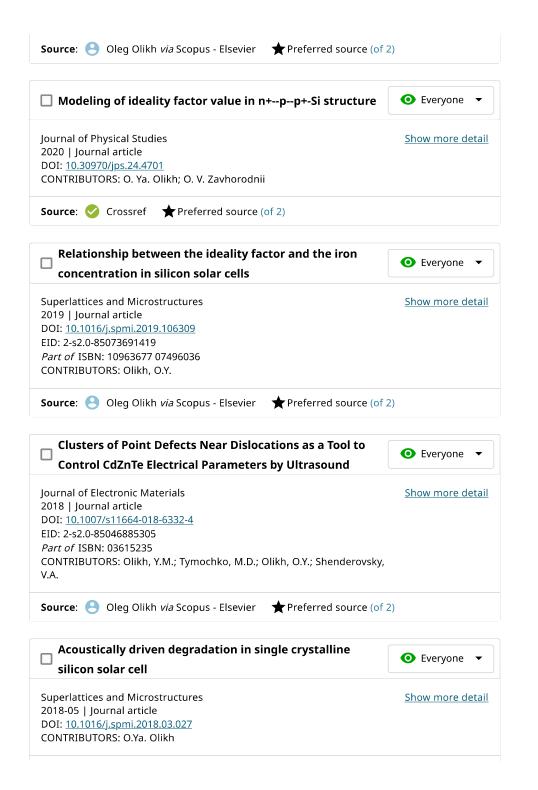
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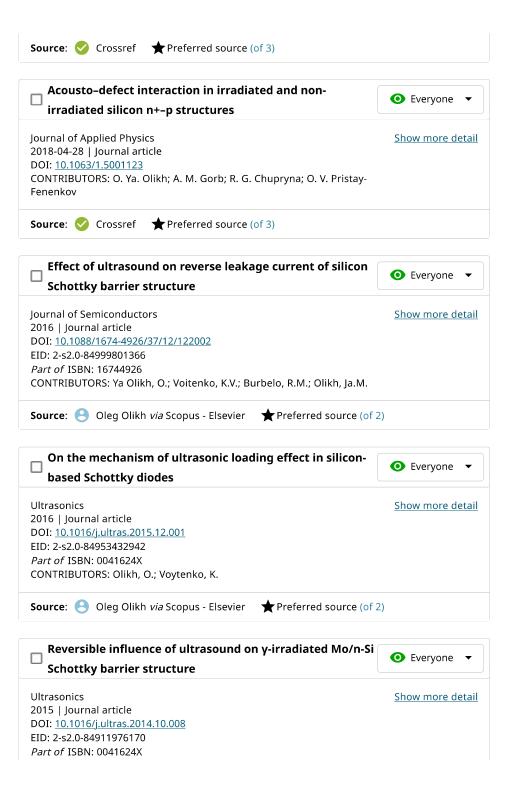
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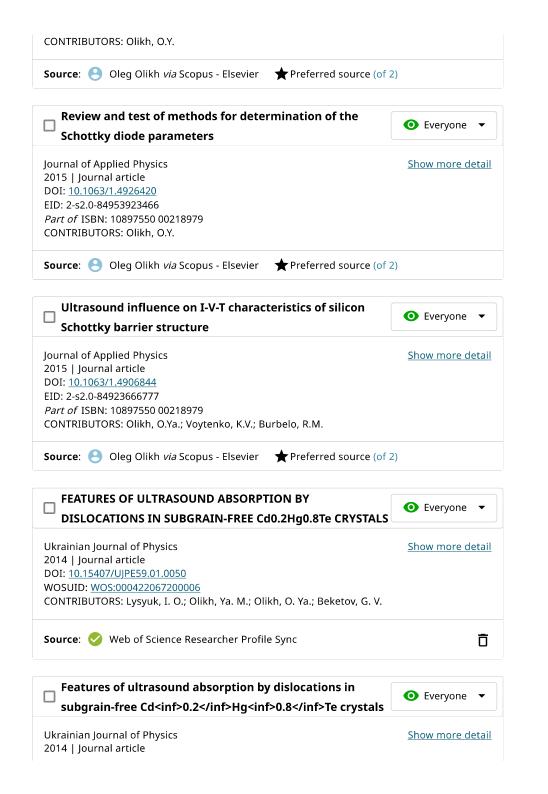


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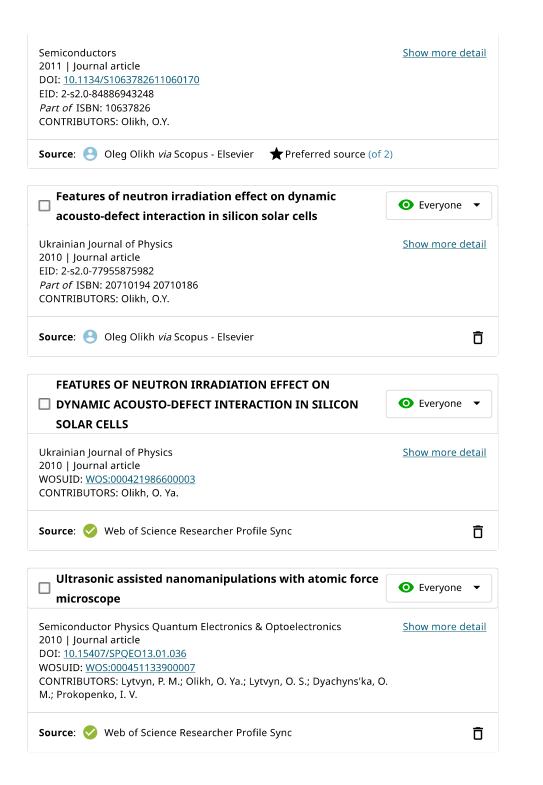


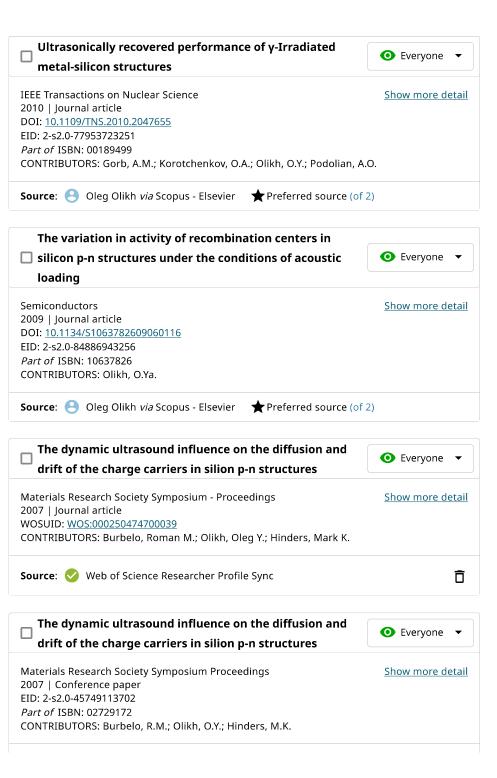


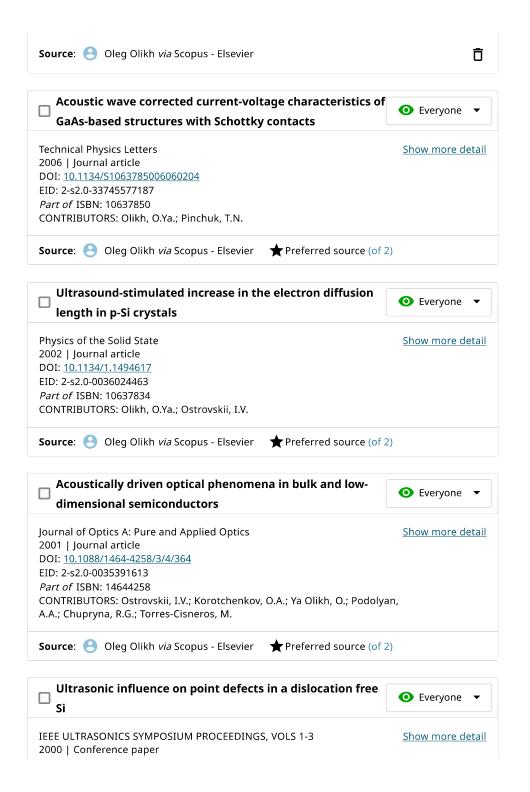




EID: 2-s2.0-84892965065 Part of ISBN: 20710194 20710186 CONTRIBUTORS: Lysyuk, I.O.; Olikh, Y.M.; Olikh, O.Y.; Beketov, G.V. **Source**: Oleg Olikh *via* Scopus - Elsevier \Box Effect of ultrasonic loading on current in Mo/n-n<sup>+</ O Everyone ▼ sup>-Si with Schottky barriers Semiconductors Show more detail 2013 | Journal article DOI: 10.1134/S106378261307018X EID: 2-s2.0-84879804840 Part of ISBN: 10637826 CONTRIBUTORS: Olikh, O.Y. **Source**: Oleg Olikh *via* Scopus - Elsevier referred source (of 2) Features of charge transport in Mo/n-Si structures with a Schottky barrier Ukrainian Journal of Physics Show more detail 2013 | Journal article DOI: 10.15407/ujpe58.02.0126 EID: 2-s2.0-84874328147 Part of ISBN: 20710194 20710186 CONTRIBUTORS: Olikh, O.Y. **Source**: Oleg Olikh *via* Scopus - Elsevier referred source (of 2) Non-monotonic y-ray influence on Mo/n-Si schottky barrier structure properties **IEEE Transactions on Nuclear Science** Show more detail 2013 | Journal article DOI: 10.1109/TNS.2012.2234137 EID: 2-s2.0-84873715135 Part of ISBN: 00189499 CONTRIBUTORS: Olikh, O.Y. **Source**: Oleg Olikh *via* Scopus - Elsevier referred source (of 2) Features of dynamic acoustically induced modification of photovoltaic parameters of silicon solar cells







DOI: 10.1109/ULTSYM.2000.922602 WOSUID: WOS:000171881300108 CONTRIBUTORS: Ostrovskii, IV; Olikh, OJ; Nadtochii, AB **Source**: Web of Science Researcher Profile Sync \Box Ultrasonic influence on point defects in a dislocation free Si Proceedings of the IEEE Ultrasonics Symposium Show more detail 2000 | Conference paper EID: 2-s2.0-0034579992 Part of ISBN: 10510117 CONTRIBUTORS: Ostrovskii, I.V.; Olikh, O.Ja.; Nadtochii, A.B. **Source**: Oleg Olikh *via* Scopus - Elsevier \Box Characterization of interface deep levels in as vapor Everyone grown EPI-GaAs Solid State Communications Show more detail 1998 | Journal article DOI: 10.1016/S0038-1098(98)00236-1 EID: 2-s2.0-0032499858 Part of ISBN: 00381098 CONTRIBUTORS: Ostrovskii, I.V.; Olikh, O.Ya. **Source**: Oleg Olikh *via* Scopus - Elsevier referred source (of 2)